

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>c</sub> = +25°C
60V	6mΩ @ V <sub>GS</sub> = 10V	80A
	8.5mΩ @ V <sub>GS</sub> = 4.5V	70A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Brushless DC motor controls
- DC-DC converters
- Load switches

## Features and Benefits

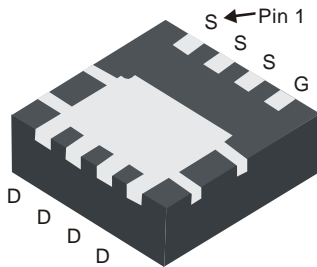
- Low R<sub>DS(ON)</sub> – Ensures On-State Losses are Minimized
- Excellent Q<sub>gd</sub> × R<sub>DS(ON)</sub> Product (FOM)
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% Unclamped Inductive Switching, Test in Production – Ensures More Reliable and Robust End Application
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMT6007LFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

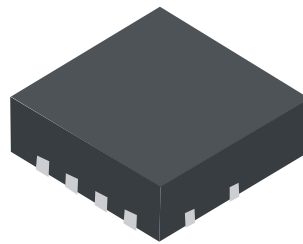
## Mechanical Data

- Package: PowerDI<sup>®</sup>3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.034 grams (Approximate)

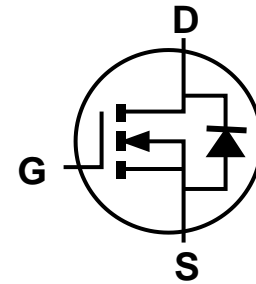
PowerDI3333-8



Bottom View



Top View



Equivalent Circuit

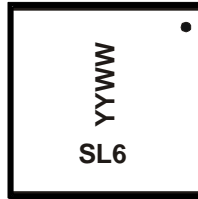
## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMT6007LFGQ-7	PowerDI3333-8	2,000	Tape & Reel
DMT6007LFGQ-13	PowerDI3333-8	3,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

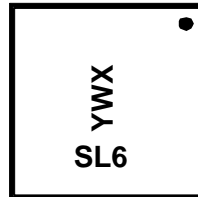
## Marking Information

Site1:



SL6 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 23 = 2023)  
 WW = Week Code (01 to 53)

Site2:



SL6 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 3 = 2023)  
 W = Week (ex: a = Week 27, z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C	I <sub>D</sub>	15
	T <sub>A</sub> = +70°C	I <sub>D</sub>	12
	T <sub>C</sub> = +25°C	I <sub>D</sub>	80
	T <sub>C</sub> = +70°C	I <sub>D</sub>	65
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	80	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	80	A
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	20	A
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	20	mJ

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	55	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	62.5	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	2	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. R<sub>θJA</sub> is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. R<sub>θJC</sub> is guaranteed by design while R<sub>θJA</sub> is determined by the user's board design.  
 6. Short duration pulse test used to minimize self-heating effect.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8	—	2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	4.5	6	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	6.5	8.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 15A
Forward Transconductance	G <sub>FS</sub>	—	100	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>iSS</sub>	—	2090	—	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oSS</sub>	—	746	—		
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	38.5	—		
Gate Resistance	R <sub>g</sub>	—	0.59	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	19.3	—	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	41.3	—		
Gate-Source Charge	Q <sub>gs</sub>	—	6.0	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	8.8	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.7	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>r</sub>	—	4.3	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	23.4	—		
Turn-Off Fall Time	t <sub>f</sub>	—	9.7	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	35.4	—	ns	I <sub>F</sub> = 20A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	38.2	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

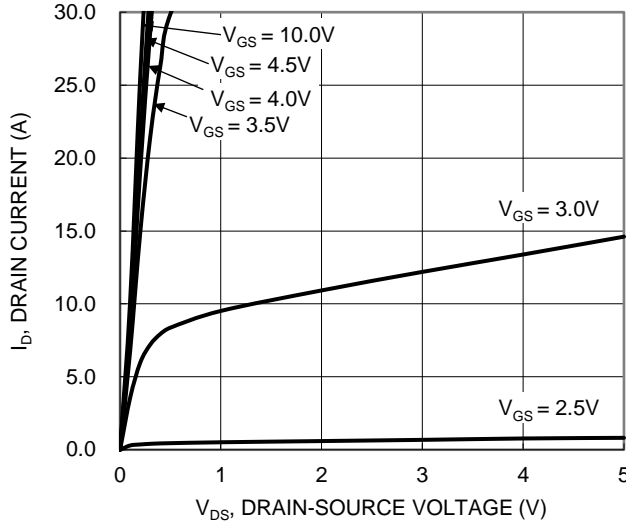


Figure 1. Typical Output Characteristic

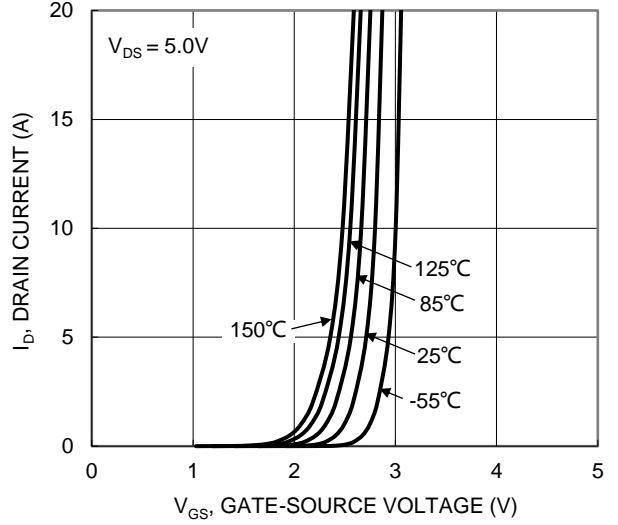


Figure 2. Typical Transfer Characteristic

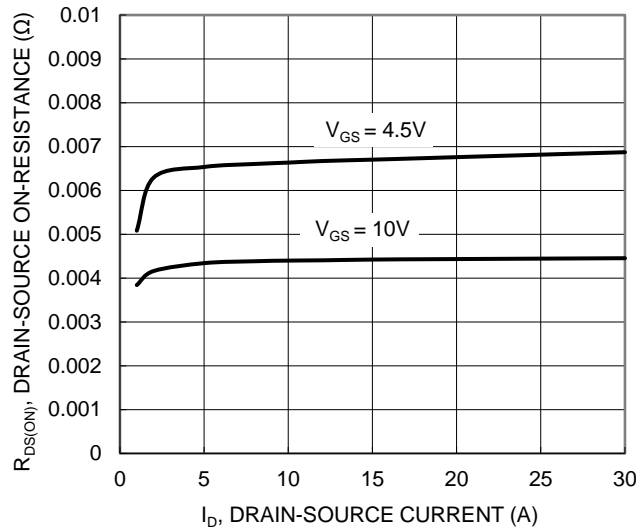


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

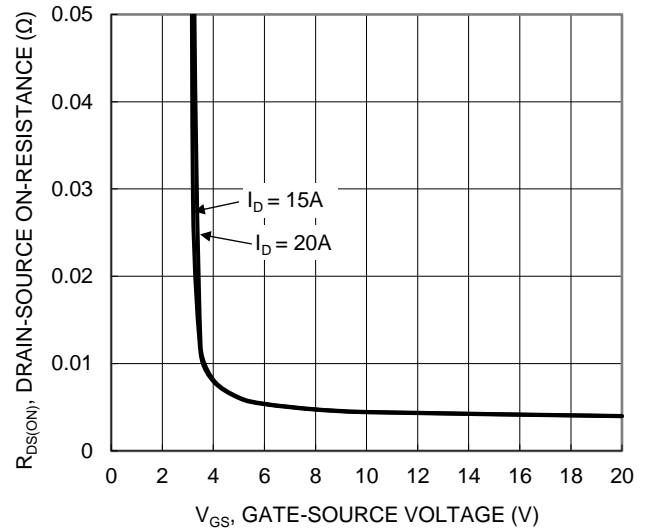


Figure 4. Typical Transfer Characteristic

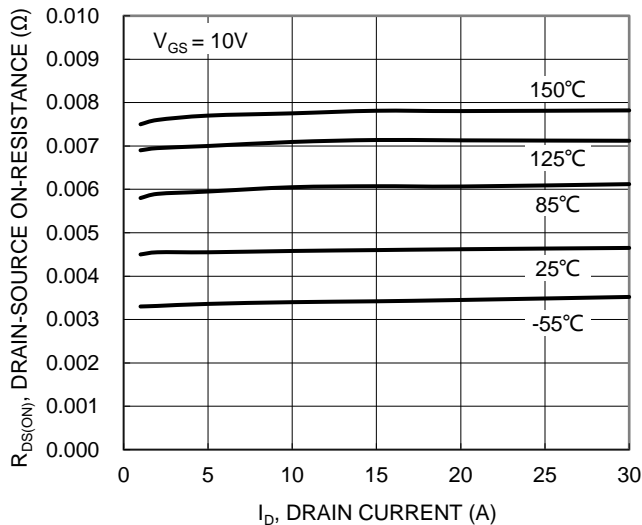


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

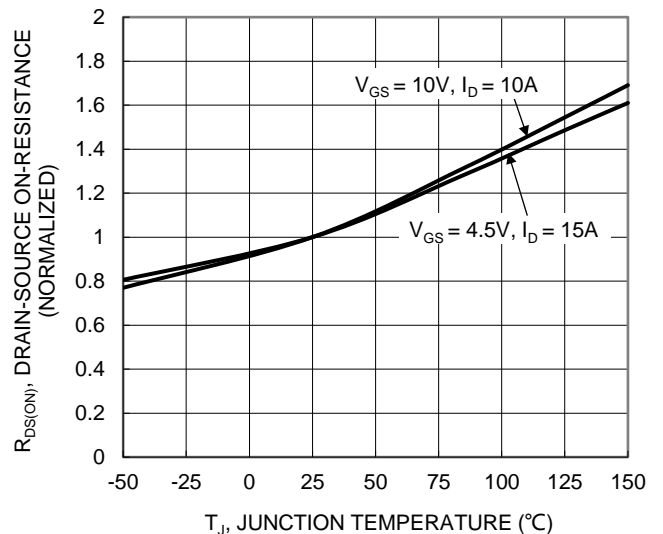
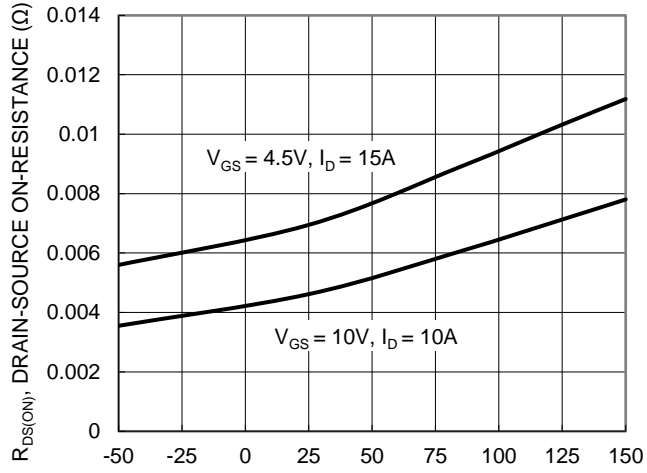
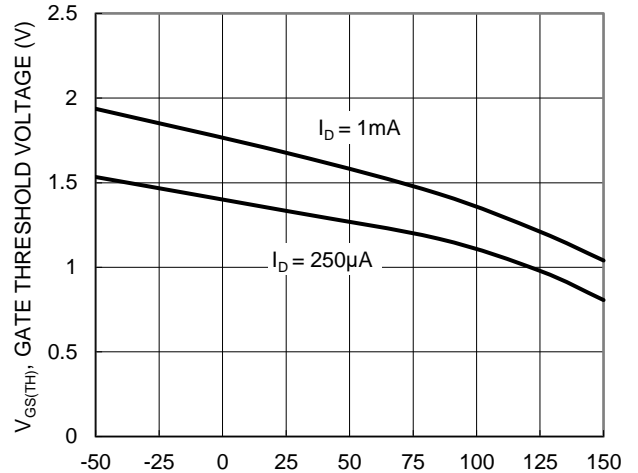


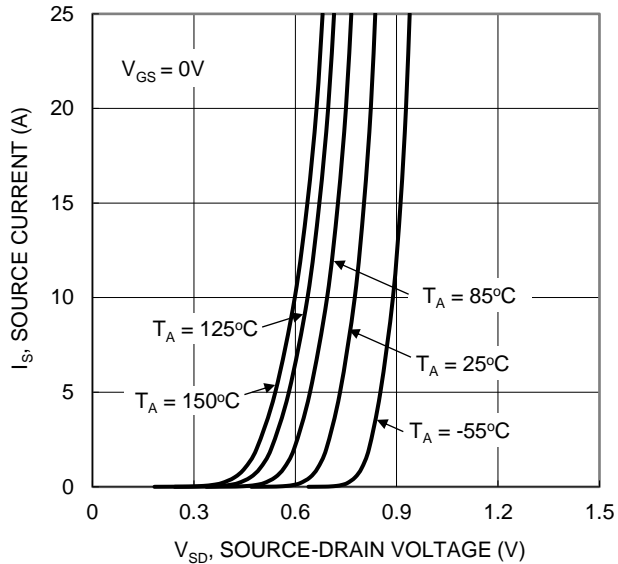
Figure 6. On-Resistance Variation with Temperature



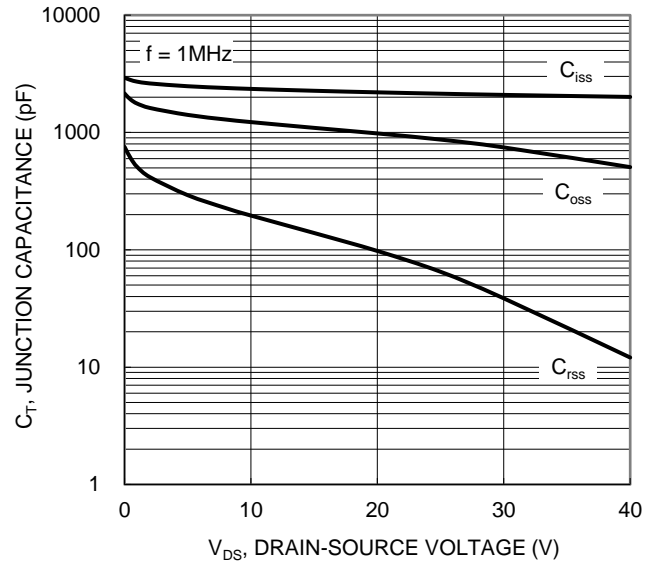
$T_J$ , JUNCTION TEMPERATURE ( $^{\circ}\text{C}$ )  
Figure 7. On-Resistance Variation with Temperature



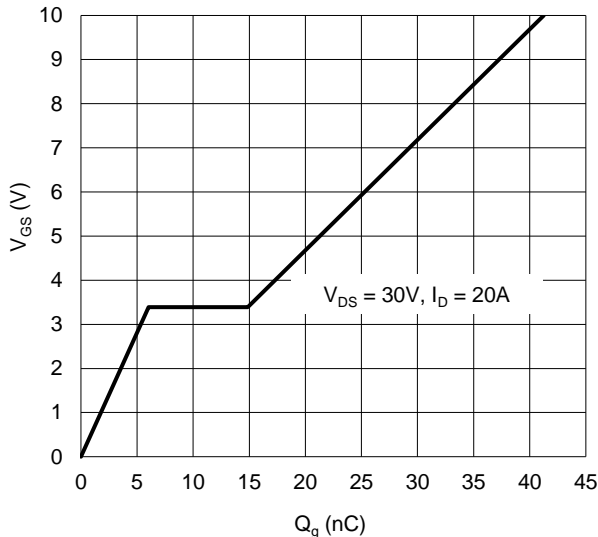
$T_J$ , JUNCTION TEMPERATURE ( $^{\circ}\text{C}$ )  
Figure 8. Gate Threshold Variation vs. Junction Temperature



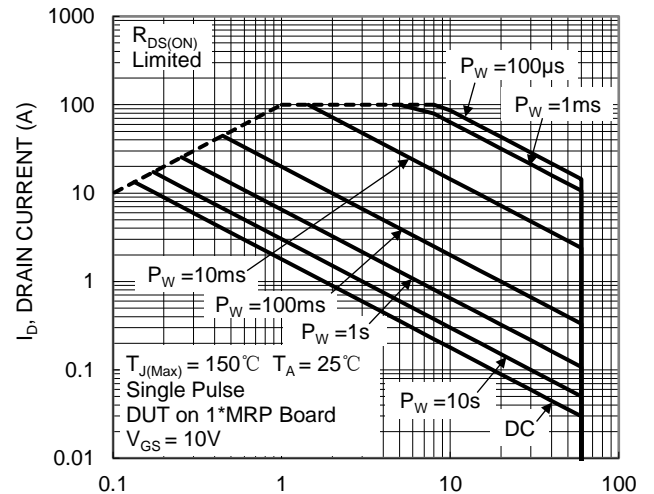
$V_{DS}$ , SOURCE-DRAIN VOLTAGE (V)  
Figure 9. Diode Forward Voltage vs. Current



$V_{DS}$ , DRAIN-SOURCE VOLTAGE (V)  
Figure 10. Typical Junction Capacitance



$Q_g$  (nC)  
Figure 11. Gate Charge



$V_{DS}$ , DRAIN-SOURCE VOLTAGE (V)  
Figure 12. SOA, Safe Operation Area

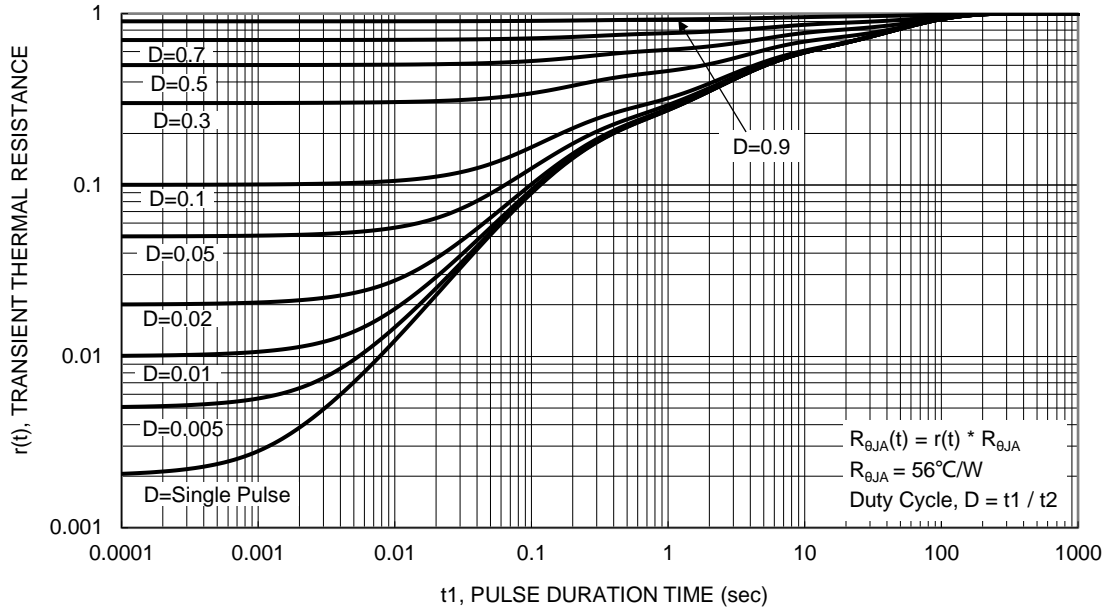
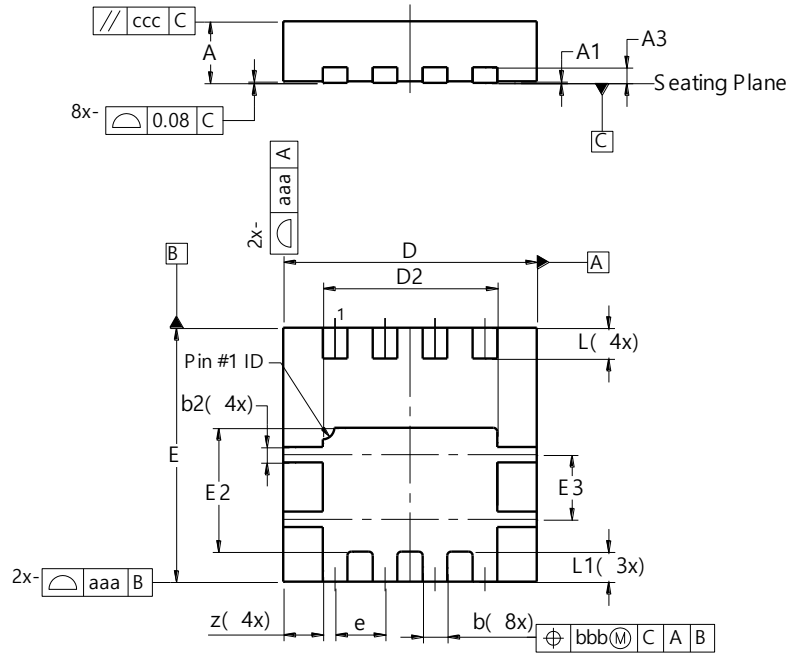


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**

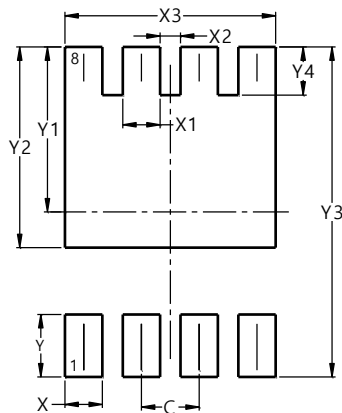


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
e	-	-	0.65
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
aaa	0.25		
bbb	0.10		
ccc	0.10		
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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